

			P %E%((
	S2XM1420N500L)%9)%))
	VDMOS		

		-	0	
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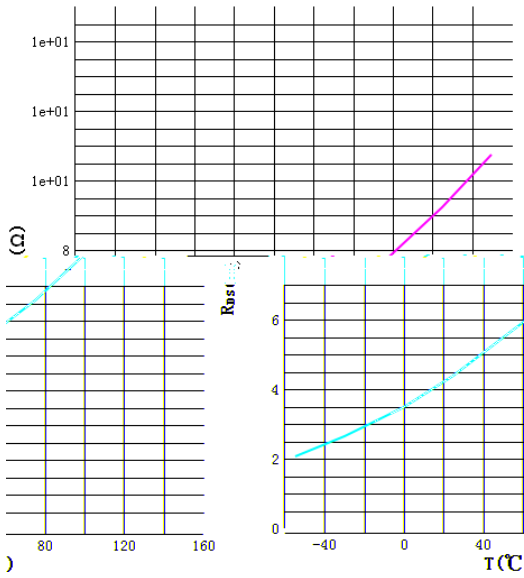
) L=10mH, V_{DD}=100V, R_g , T_f=25

e 5 -

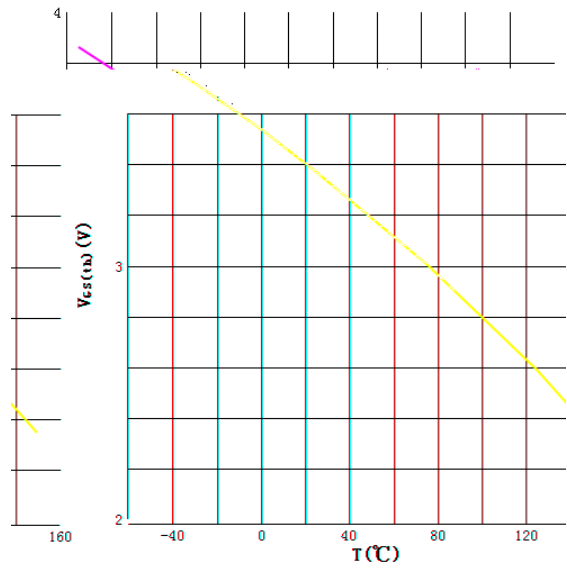
	BV _{DSS}	V _{GS} =0V	I _D	2	500	-	-	V
	V _{TH}	V _{GS} =V _{DS}	I _D	2	2			

			P %E%((
	S2XM1420N500L)%9)%))
	VDMOS		

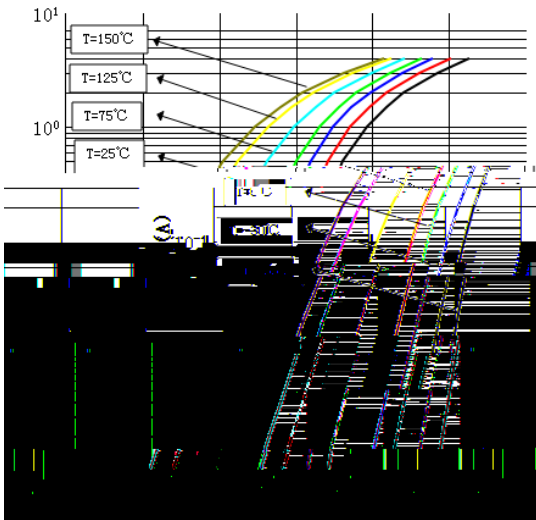
$R_{DS(on)}-T$ ($V_{GS}=10V, I_D=5A$)



$V_{GS(th)}-T$ ($V_{DS}=V_{GS}, I_D=250\mu A$)



I_S-V_{FSD}



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